PNP Epitaxial Planar Silicon Transistors



2SA1798

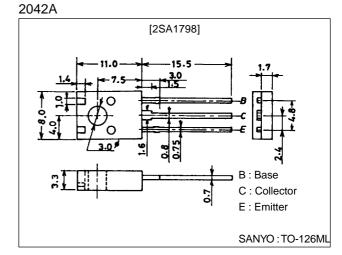
20V/8A Switching Applications

Features

- \cdot Adoption of MBIT processes.
- \cdot Low saturation voltage.
- \cdot Fast switching speed.
- · Large current capacity.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-25	V
Collector-to-Emitter Voltage	VCEO		-20	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	ι _C		-8	A
Colletor Current (Pulse)	ICP		-12	A
Base Current	Ι _Β		-1.5	A
Collector Dissipation	PC		1.5	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

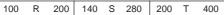
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-20V, I _E =0			-1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0			-1	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =-2V, I _C =-500mA	100*		400*	
	h _{FE} 2	V _{CE} =-2V, I _C =-6A	60			
Gain-Bandwidth Product	fT	V _{CE} =-2V, I _C =-500mA		200		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		85		pF

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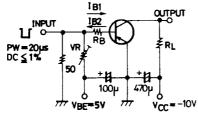
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-5A, I _B =-250mA		-220	-400	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-5A, I _B =-250mA		-1	-1.3	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0	-25			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =−1mA, R _{BE} =∞	-20			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Turn-ON Time	ton	See specified Test Circuit		30		ns
Storage Time	tstg	See specified Test Circuit		200		ns
Fall Time	t _f	See specified Test Circuit		15		ns

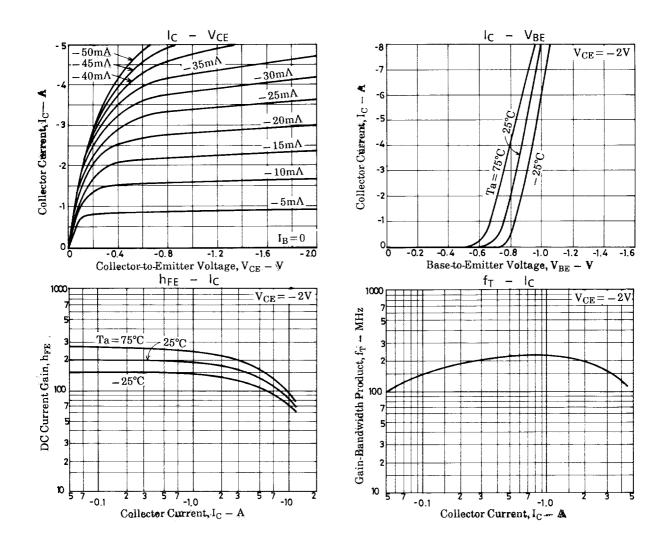
 \ast : The 2SA1798 is classified by 500mA h_{FE} as follows :

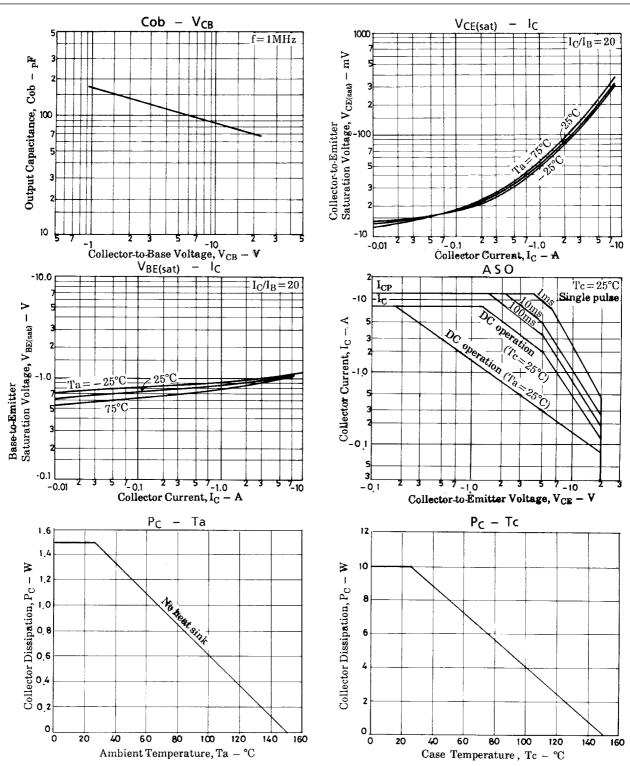


Switching Time Test Circuit



 $\begin{array}{l} 20I_{B1} {=} {-} 20I_{B2} {=} I_C {=} {-} 5A \\ \text{Unit (resistance : } \Omega, \ capacitance : F)} \end{array}$





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